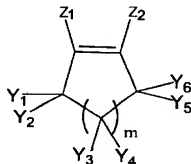


ABSTRACT OF THE DISCLOSURE

Photoresist monomers of following Formula 1,
photoresist polymers thereof, and photoresist
compositions containing the same. The photoresist
5 polymers include a repeating unit comprising the
photoresist monomer of Formula 1 as a comonomer and the
photoresist compositions containing the same have
excellent etching resistance, heat resistance and
adhesiveness to a wafer, and are developable in aqueous
10 tetramethylammonium hydroxide (TMAH) solutions. In
addition, the photoresist compositions have a low light
absorbance at 157nm wavelength, and thus are suitable for
a photolithography process using ultraviolet light
sources such as VUV (157nm) in fabricating a minute
15 circuit for a high integration semiconductor device.

Formula 1



wherein Y₁, Y₂, Y₃, Y₄, Y₅, Y₆, Z₁, Z₂ and m are
defined in the specification.